查询KTD998供应商 捷多邦，专业PCB打样工厂，24小时加急出货

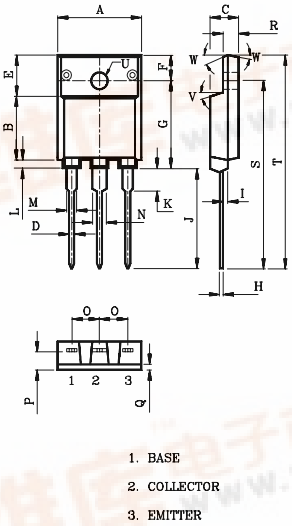
KEL
KOREA ELECTRONICS CO.,LTD.

SEMICONDUCTOR
TECHNICAL DATA

KTD998
TRIPLE DIFFUSED NPN TRANSISTOR

HIGH POWER AMPLIFIER APPLICATION.

FEATURES
- Recommended for 45~50W Audio Frequency Amplifier Output Stage.
- Complementary to KTB778.



DIM	MILLIMETERS
A	16.30 MAX
B	12.00±0.30
C	5.50±0.20
D	1.20 MAX
E	8.00
F	5.00
G	17.00±0.30
H	0.60+0.15/-0.10
I	2.50
J	20.0±0.1
K	4.00
L	2.00
M	2.20 MAX
N	3.05 MAX
O	5.45
P	3.50
Q	1.00
R	3.00±0.20
S	37.0
T	42.0
U	ø3.40+0.15/-0.10
V	10°
W	8°

1. BASE
2. COLLECTOR
3. EMITTER

TO-3P(H)IS

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	10	A
Base Current	I_B	1.0	A
Collector Power Dissipation (Tc=25℃)	P_C	80	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=120V, I_E=0	-	-	10	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	-	-	10	μA
Collector-emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=50mA, I_B=0	120	-	-	V
DC Current Gain	h_{FE}(Note)	V_{CE}=5V, I_C=1A	55	-	160	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=5A, I_B=0.5A	-	-	2.5	V
Base-Emitter Voltage	V_{BE}	V_{CE}=5V, I_C=5A	-	-	1.5	V
Transition Frequency	f_T	V_{CE}=5V, I_C=1A	-	12	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	-	170	-	pF

Note: h_{FE} Classification R:55~110, O:80~160

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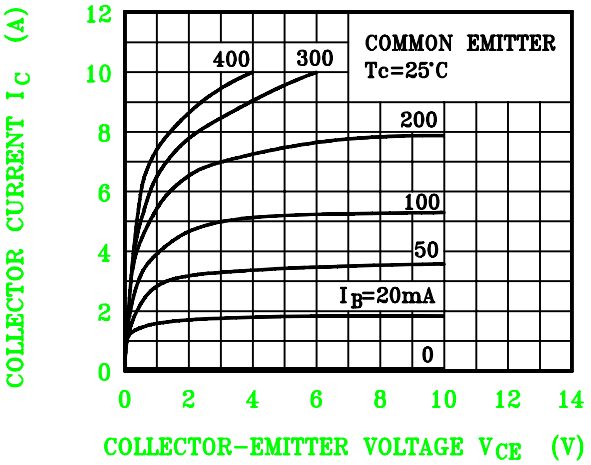
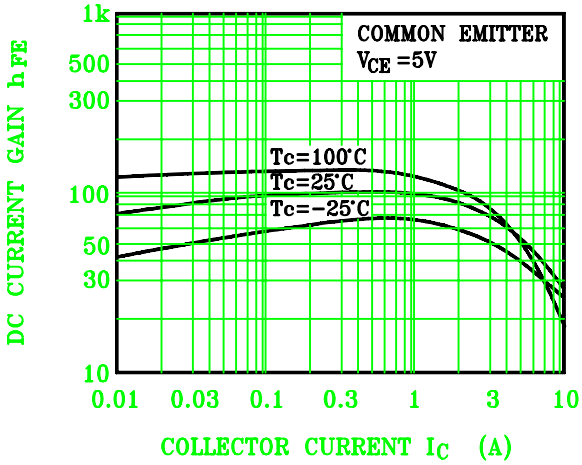
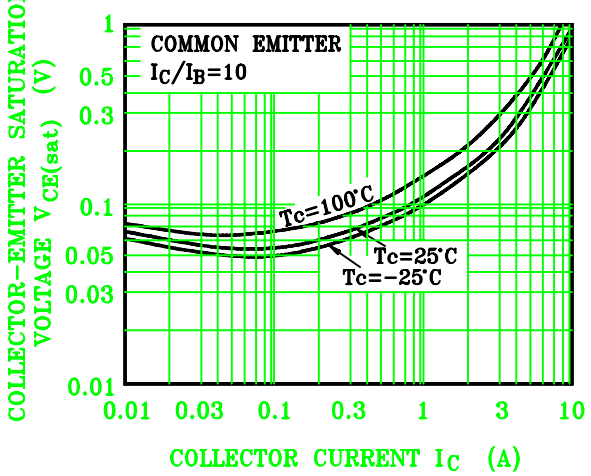
I_C – V_{CE}



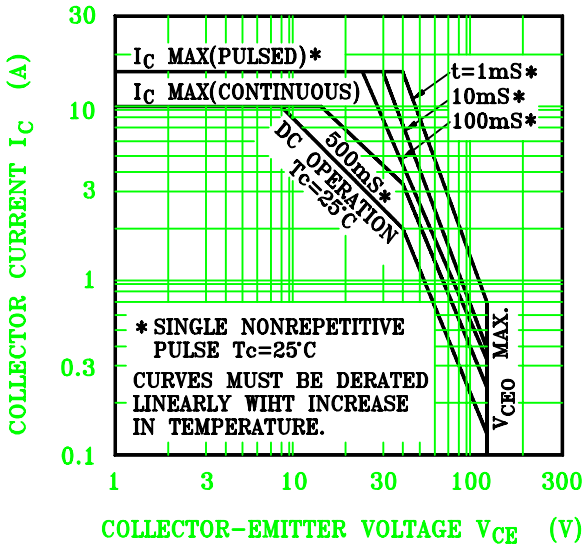
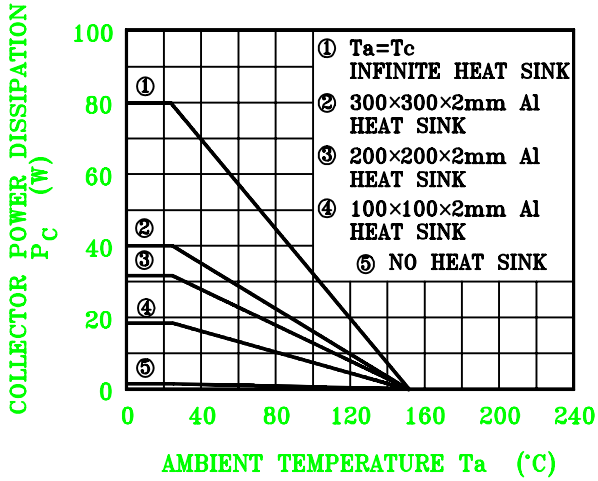
h_{FE} – I_C



$V_{CE(sat)}$ – I_C



SAFE OPERATING AREA



P_C – Ta